

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Priority Application Serial No. .... 09/905,210  
Priority Filing Date ..... July 13, 2001  
 Inventor ..... Cem Basceri et al.  
 Assignee ..... Micron Technology, Inc.  
Priority Group Art Unit ..... 1762  
Priority Examiner ..... Eric B. Fuller  
 Attorney Docket No. .... MI22-2501  
 Customer No. .... 021567  
 Title: Chemical Vapor Deposition Methods of Forming a Barium Strontium  
 Titanate Comprising Dielectric Layer Having a Varied Concentration of  
 Barium and Strontium With the Layer

**INFORMATION DISCLOSURE STATEMENT**

References -- See Attached Form PTO-1449

The attached form PTO-1449 is submitted in compliance with  
 37 CFR §1.56. Pursuant to 1276 OG 55, August 5, 2003, no copies of cited U.S.  
 patents or U.S. patent application publications are included, as the date of filing  
 of this patent application occurs after June 30, 2003. No admission is made  
 regarding whether all the listed references are prior art.

Respectfully submitted,

Dated: \_\_\_\_\_

1-30-04

By: \_\_\_\_\_



Mark S. Matkin  
 Reg. No. 32,268

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-2501		PRIORITY SERIAL NO. 09/905,320	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT: Cem Basceri et al.			
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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